

SEMITOP® 2

IGBT Module

SK 9GD065

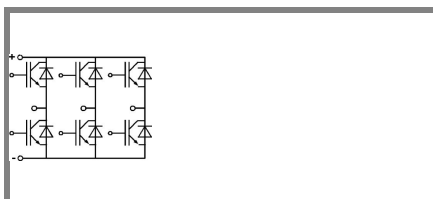
Preliminary Data

Features

- Compact design
- One screw mounting
- Heat transfer and isolation through direct copper bonded aluminium oxide ceramic (DCB)
- Ultrafast NPT technology IGBT
- CAL technology FWD

Typical Applications

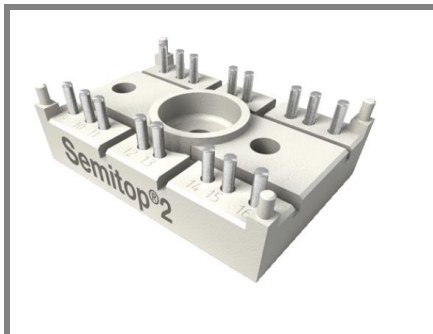
- Switching (not for linear use)
- Inverter
- Switched mode power supplies
- UPS



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Absolute Maximum Ratings		$T_s = 25\text{ °C}$, unless otherwise specified	
Symbol	Conditions	Values	Units
IGBT			
V_{CES}	$T_j = 25\text{ °C}$	600	V
I_C	$T_j = 125\text{ °C}$	$T_s = 25\text{ °C}$	11 A
		$T_s = 80\text{ °C}$	8 A
I_{CRM}	$I_{CRM} = 2 \times I_{Cnom}$	12	A
V_{GES}		± 20	V
t_{psc}	$V_{CC} = 300\text{ V}; V_{GE} \leq 20\text{ V}; T_j = 125\text{ °C}$ $V_{CES} < 600\text{ V}$	10	μs
Inverse Diode			
I_F	$T_j = 125\text{ °C}$	$T_s = 25\text{ °C}$	22 A
		$T_s = 80\text{ °C}$	15 A
I_{FRM}	$I_{FRM} = 2 \times I_{Fnom}$	30	A
Module			
$I_{t(RMS)}$			A
T_{vj}		-40 ... +150	$^{\circ}\text{C}$
T_{stg}		-40 ... +125	$^{\circ}\text{C}$
V_{isol}	AC, 1 min.	2500	V

Characteristics		$T_s = 25\text{ °C}$, unless otherwise specified			
Symbol	Conditions	min.	typ.	max.	Units
IGBT					
$V_{GE(th)}$	$V_{GE} = V_{CE}, I_C = 0,2\text{ mA}$	3	4	5	V
I_{CES}	$V_{GE} = 0\text{ V}, V_{CE} = V_{CES}$	$T_j = 25\text{ °C}$		0,03	mA
		$T_j = 125\text{ °C}$			mA
I_{GES}	$V_{CE} = 0\text{ V}, V_{GE} = 20\text{ V}$	$T_j = 25\text{ °C}$		120	nA
		$T_j = 125\text{ °C}$			nA
V_{CE0}		$T_j = 25\text{ °C}$	1,2		V
		$T_j = 125\text{ °C}$	1,1		V
r_{CE}	$V_{GE} = 15\text{ V}$	$T_j = 25\text{ °C}$	133		$\text{m}\Omega$
		$T_j = 125\text{ °C}$	183		$\text{m}\Omega$
$V_{CE(sat)}$	$I_{Cnom} = 6\text{ A}, V_{GE} = 15\text{ V}$	$T_j = 25\text{ °C}_{chiplev.}$	2	2,5	V
		$T_j = 125\text{ °C}_{chiplev.}$	2,2	2,7	V
C_{ies}	$V_{CE} = 25, V_{GE} = 0\text{ V}$	$f = 1\text{ MHz}$	0,35		nF
C_{oes}			0,038		nF
C_{res}			0,023		nF
$t_{d(on)}$	$R_{Gon} = 120\ \Omega$	$V_{CC} = 300\text{ V}$ $I_{Cnom} = 6\text{ A}$	20		ns
t_r			25		ns
E_{on}	$R_{Goff} = 120\ \Omega$	$T_j = 125\text{ °C}$ $V_{GE} = \pm 15\text{ V}$	0,22		mJ
$t_{d(off)}$			145		ns
t_f			25		ns
E_{off}			0,12		mJ
$R_{th(j-s)}$	per IGBT			2,6	K/W



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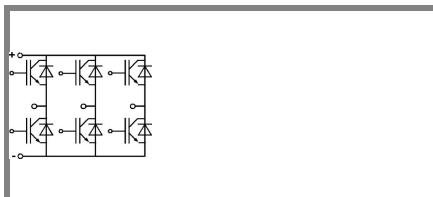
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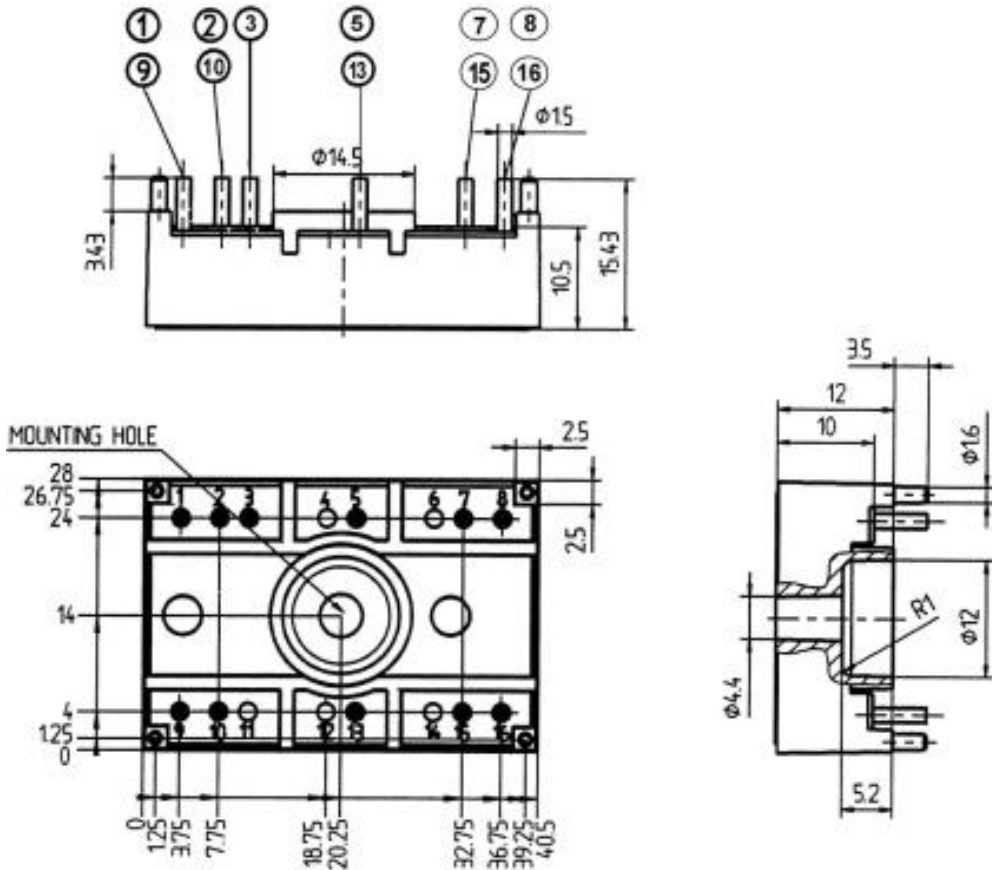
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Characteristics

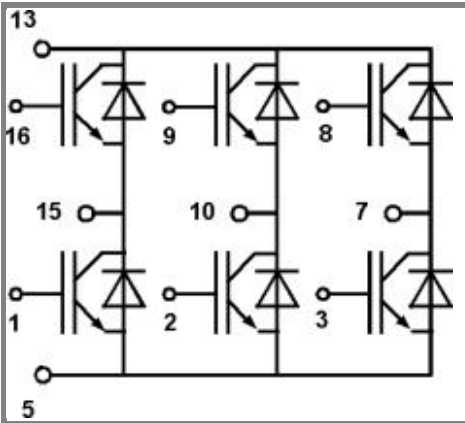
Symbol	Conditions	min.	typ.	max.	Units
Inverse Diode					
$V_F = V_{EC}$	$I_{Fnom} = 15 \text{ A}; V_{GE} = 0 \text{ V}$	$T_j = 25 \text{ }^\circ\text{C}_{\text{chiplev.}}$	1,4	1,7	V
		$T_j = 125 \text{ }^\circ\text{C}_{\text{chiplev.}}$	1,4	1,7	V
V_{F0}		$T_j = 25 \text{ }^\circ\text{C}$	1	1,1	V
		$T_j = 125 \text{ }^\circ\text{C}$	0,9	1	V
r_F		$T_j = 25 \text{ }^\circ\text{C}$	30	40	mΩ
		$T_j = 125 \text{ }^\circ\text{C}$	33	47	mΩ
I_{RRM}	$I_{Fnom} = 15 \text{ A}$		22		A
Q_{rr}	$di/dt = 1100 \text{ A}/\mu\text{s}$		1,5		μC
E_{rr}	$V_{CC} = 300\text{V}$		0,31		mJ
$R_{th(j-s)D}$	per diode			2,3	K/W
M_s	to heat sink			2	Nm
w			21		g

This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, Chapter IX.

This technical information specifies semiconductor devices but promises no characteristics. No warranty or guarantee expressed or implied is made regarding delivery, performance or suitability.



Case T47 (Suggested hole diameter, in the PCB, for solder pins and plastic mounting pins: 2mm)



Case T 47

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